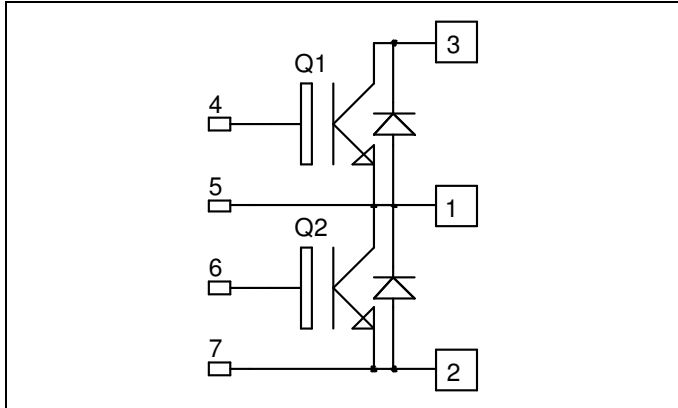


*Phase Leg  
Trench IGBT® Power Module*

**V<sub>CES</sub> = 1200V**  
**I<sub>C</sub> = 35A @ T<sub>c</sub> = 80°C**



**Application**

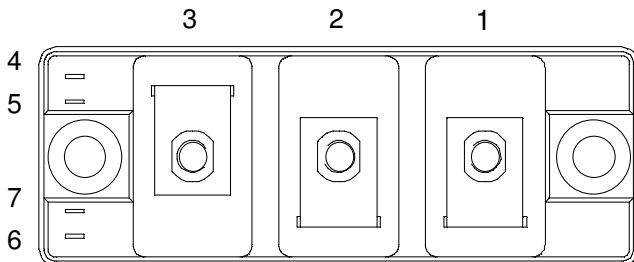
- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

**Features**

- Trench + Field Stop IGBT® Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - Avalanche energy rated
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
  - M5 power connectors
- High level of integration

**Benefits**

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of V<sub>CESat</sub>



**Absolute maximum ratings**

Symbol	Parameter	Max ratings	Unit
V <sub>CES</sub>	Collector - Emitter Breakdown Voltage	1200	V
I <sub>C</sub>	Continuous Collector Current	T <sub>C</sub> = 25°C	55
		T <sub>C</sub> = 80°C	35
I <sub>CM</sub>	Pulsed Collector Current	T <sub>C</sub> = 25°C	70
V <sub>GE</sub>	Gate - Emitter Voltage	±20	V
P <sub>D</sub>	Maximum Power Dissipation	T <sub>C</sub> = 25°C	205
RBSOA	Reverse Bias Safe Operation Area	T <sub>j</sub> = 125°C	70A@1200V

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

## Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$BV_{CES}$	Collector - Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 1.5mA$	1200			V
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$			5	mA
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15V$ $I_C = 35A$		$T_j = 25^\circ\text{C}$ 1.7 $T_j = 125^\circ\text{C}$ 2.0	2.1	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.5mA$	5.0	5.8	6.5	V
$I_{GES}$	Gate - Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			400	nA

## Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$		2.5		nF
$C_{res}$	Reverse Transfer Capacitance	$f = 1MHz$		0.1		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 35A$ $R_G = 27\Omega$		150		ns
$T_r$	Rise Time			90		
$T_{d(off)}$	Turn-off Delay Time			550		
$T_f$	Fall Time			130		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $125^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 35A$ $R_G = 27\Omega$		180		ns
$T_r$	Rise Time			100		
$T_{d(off)}$	Turn-off Delay Time			650		
$T_f$	Fall Time			180		

## Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_F$	Diode Forward Voltage	$I_F = 35A$ $V_{GE} = 0V$		$T_j = 25^\circ\text{C}$ 1.6 $T_j = 125^\circ\text{C}$ 1.6	2.1	V
$E_{rec}$	Reverse Recovery Energy	$I_F = 35A$ $V_R = 600V$ $di/dt = 990A/\mu s$		$T_j = 125^\circ\text{C}$ 2.7		mJ
$Q_{rr}$	Reverse Recovery Charge	$I_F = 35A$ $V_R = 600V$ $di/dt = 990A/\mu s$		$T_j = 25^\circ\text{C}$ 3.7 $T_j = 125^\circ\text{C}$ 6.8		$\mu C$

## Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
$R_{thJC}$	Junction to Case	IGBT			0.6	$^\circ\text{C}/W$
		Diode			0.95	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case $t = 1$ min, $I_{isol} < 1mA, 50/60Hz$	2500			V	
$T_j$	Operating junction temperature range	-40		150	$^\circ\text{C}$	
$T_{STG}$	Storage Temperature Range	-40		125		
$T_C$	Operating Case Temperature	-40		125		
Torque	Mounting torque	For terminals	M5	2	3.5	N.m
		To Heatsink	M6	3	5	
Wt	Package Weight				180	g

## Package outline

